



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

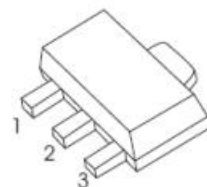
PXT2907A

SOT-89 Bipolar Transistor 双极型三极管

■ Features 特点

PNP Switching 开关

1. BASE
2. COLLECTOR
3. EMITTER



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-60	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-60	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-600	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

■ Device Marking 产品打标

PXT2907A=P2F

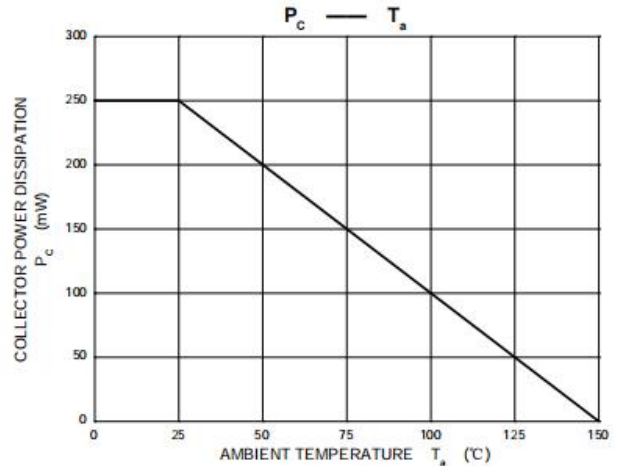
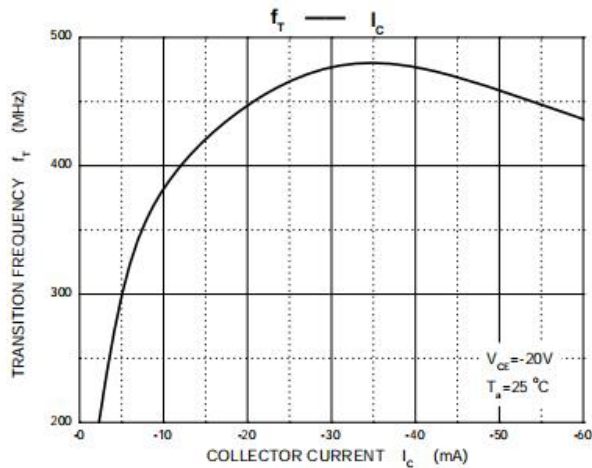
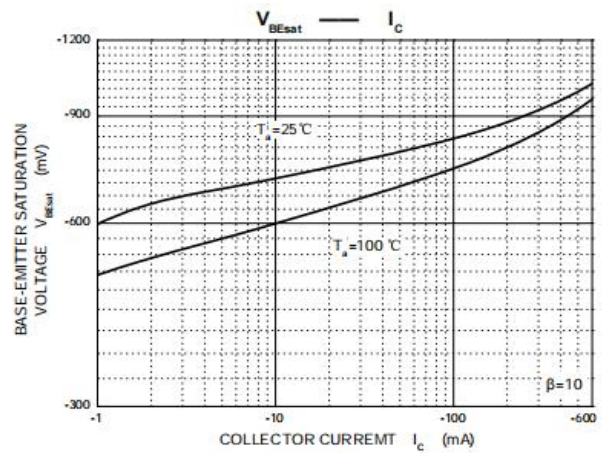
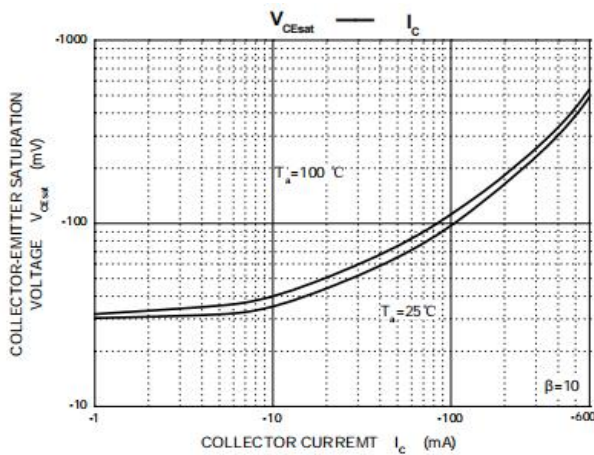
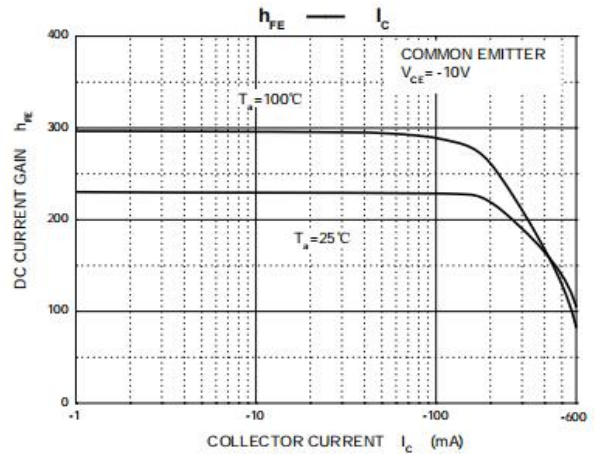
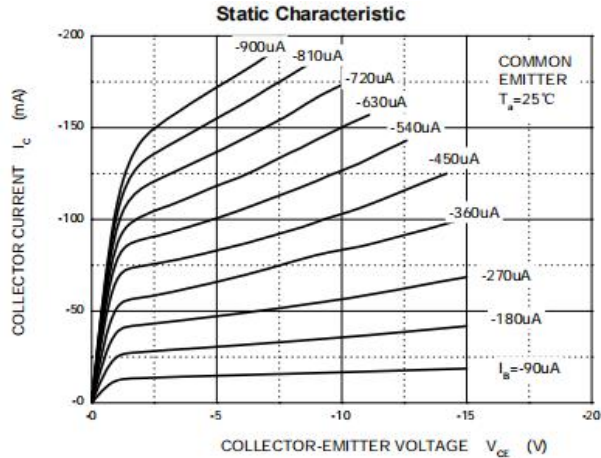


■ Electrical Characteristics 电特性

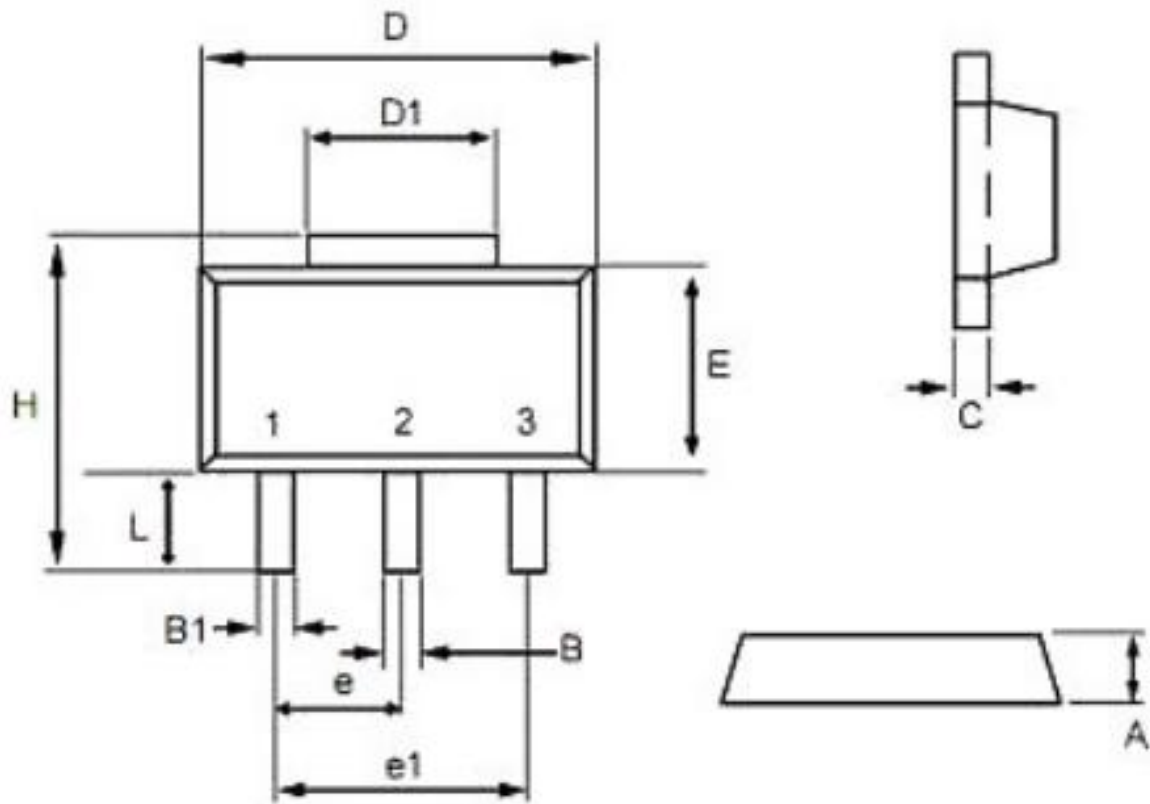
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C = -1\text{mA}$, $I_E = 0$)	BV_{CBO}	-60	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C = -10\text{mA}$, $I_B = 0$)	BV_{CEO}	-60	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E = -1\text{mA}$, $I_C = 0$)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{CB} = -50\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流($V_{CE} = -35\text{V}$, $V_{BE} = 0.5\text{V}$)	I_{CEX}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{EB} = -4\text{V}$, $I_C = 0$)	I_{EBO}	—	—	-100	nA
DC Current Gain($V_{CE} = -10\text{V}$, $I_C = -0.1\text{mA}$) 直流电流增益($V_{CE} = -10\text{V}$, $I_C = -150\text{mA}$) ($V_{CE} = -10\text{V}$, $I_C = -500\text{mA}$)	H_{FE}	75 100 50	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C = -500\text{mA}$, $I_B = -50\text{mA}$) ($I_C = -150\text{mA}$, $I_B = -15\text{mA}$)	$V_{CE(sat)}$	—	—	-0.6 -0.4	V
Base-Emitter Saturation Voltage 基极发射极饱和压降($I_C = -500\text{mA}$, $I_B = -50\text{mA}$) ($I_C = -150\text{mA}$, $I_B = -15\text{mA}$)	$V_{BE(sat)}$	—	—	-2.6 -1.3	V
Transition Frequency 特征频率($V_{CE} = -20\text{V}$, $I_C = -20\text{mA}$)	f_T	200	—	—	MHz
Delay Time 延迟时间 ($V_{CC} = -30\text{V}$, $V_{BE} = 0.5\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$)	t_d	—	—	10	ns
Rise Time 上升时间 ($V_{CC} = -30\text{V}$, $V_{BE} = 0.5\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$)	t_r	—	—	25	ns
Storage Time 贮存时间 ($V_{CC} = -30\text{V}$, $V_{BE} = 0.5\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$)	t_s	—	—	225	ns
Fall Time 下降时间 ($V_{CC} = -30\text{V}$, $V_{BE} = 0.5\text{V}$, $I_C = -150\text{mA}$, $I_{B1} = -15\text{mA}$)	t_f	—	—	60	ns

Typical Characteristic Curve 典型特性曲线



Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047